

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings of claims in the application:

Listing of Claims:

1. (Previously presented) A method for preventing to form a spacer undercut in SEG Pre-clean process, comprising:
 - providing a semiconductor substrate;
 - forming a gate structure on said semiconductor substrate;
 - forming a spacer of double-film structure on a side-wall of said gate structure, wherein said spacer of double-film structure comprises a first spacer and a second spacer, said first spacer being formed between said side-wall of said gate structure and said second spacer;
 - removing a portion of a surface of said semiconductor substrate by using a DHF (hydrofluoric acid diluted in deionized water) solution to remove a native oxide layer on said surface of said semiconductor substrate; and
 - etching said first spacer and said second spacer, wherein an etching rate of said second spacer is faster than an etching rate of said first spacer.
2. Canceled.
3. (Previously presented) The method for preventing to form a spacer undercut in SEG Pre-clean process according to claim 1, wherein a volume ratio for hydrofluoric acid to deionized water is about 1:10 – 1:100 in said DHF solution.
4. (Previously presented) The method for preventing to form a spacer undercut in SEG Pre-clean process according to claim 1, wherein etching said first spacer and said second spacer comprises a HFEG (HF diluted by ethylene glycol) solution is utilized.

5. (Original) The method for preventing to form a spacer undercut in SEG Pre-clean process according to claim 4, wherein a volume ratio for hydrofluoric acid to ethylene glycol is 0 – 4% in said HFEG solution.

6. – 7. Cancelled

8. (Original) The method for preventing to form a spacer undercut in SEG Pre-clean process according to claim 1, wherein said first spacer comprises silicon dioxide.

9. (Original) The method for preventing to form a spacer undercut in SEG Pre-clean process according to claim 8, wherein said second spacer comprises silicone nitride.

10. – 18. Cancelled.

19. (Previously presented) The method for preventing to form a spacer undercut in SEG Pre-clean process according to claim 1, wherein formation of said raised source/drain is formed by selective epitaxial growth (SEG) method.

20. (Currently amended) A method for preventing to form a spacer undercut in SEG Pre-clean process comprising:

providing a semiconductor substrate;

forming a gate structure on said semiconductor substrate, wherein said gate structure comprises a gate oxide and a polysilicon gate electrode, said polysilicon gate electrode on said gate oxide;

forming a first spacer ~~comprises~~ comprising silicon dioxide on a side-wall of said polysilicon gate electrode and said gate oxide;

forming a second spacer ~~comprises~~ comprising silicon nitride on a side-wall of said first spacer;

performing a first Pre-clean process, using a DHF solution to clean a surface of said semiconductor substrate;

performing a second [[HFEG]] Pre-clean process, using a HFEG solution to clean a portion of said surface of said semiconductor substrate and a portion of said first spacer and a portion of said second spacer; and

forming a raised source/drain on said surface of said semiconductor substrate.

21. Cancelled.

22. (Original) The method for preventing to form a spacer undercut in SEG Pre-clean process according to claim 20, wherein a volume ratio for hydrofluoric acid to ethylene glycol is 0 – 4% in said HFEG solution.

23. (Original) The method for preventing to form a spacer undercut in SEG Pre-clean process according to claim 20, wherein said raised source/drain is formed by selective epitaxial growth (SEG) method.

24. (Original) The method for preventing to form a spacer undercut in SEG Pre-clean process according to claim 23, wherein said selective epitaxial growth (SEG) method for said raised source/drain is selected from a group consisting of low pressure chemical vapor deposition and ultra-high vacuum chemical vapor deposition.

25. (Original) The method for preventing to form a spacer undercut in SEG Pre-clean process according to claim 23, wherein said raised source/drain comprises epitaxial silicon.

26. Cancelled.

27. (Currently amended) The method for preventing to form a spacer undercut in SEG Pre-clean process according to claim [[26]] 20, wherein a volume ratio for hydrofluoric acid to deionized water is about 1:10 – 1:100 in said DHF solution.